

PARAMETER		SYMBOL	HLMP						TEST
			-2300	-2350	-2655	-2670	-2685	UNIT	CONDITIONS
Luminous	min.		6.0	13	13	13	22	mcd	I <sub>F</sub> =20 mA
Intensity	typ.	l <sub>v</sub>	23	45	43	45	80	mcd	I <sub>F</sub> =20 mA
	typ.		30	50	50	50	100	mcd	I <sub>F</sub> =60 mA pK, 1:3 D.F
Forward	max.	VF	2.6	2.6	2.6	2.6	2.6	V	I <sub>r</sub> =20 mA
voltage	typ.	VF	2.0	2.0	2.0	2.0	2.0	v	1F-20 IIIA
Peak wavelength	typ.	$\lambda_{p}$	630	630	630	630	630	nm	
Dominant wavelength	typ.	$\lambda_{\sigma}$	626	626	626	626	626	nm	
Capacitance	typ.	С	45	45	45	45	45	pF	V <sub>F</sub> =0, f=1 MHz
Reverse voltage	min.	V <sub>R</sub>	6	6	6	6	6	v	I <sub>R</sub> =100 μA
Thermal resistance	typ.	θ <sub>JL</sub>	150	150	150	150	150	°C/W/ LED chip	

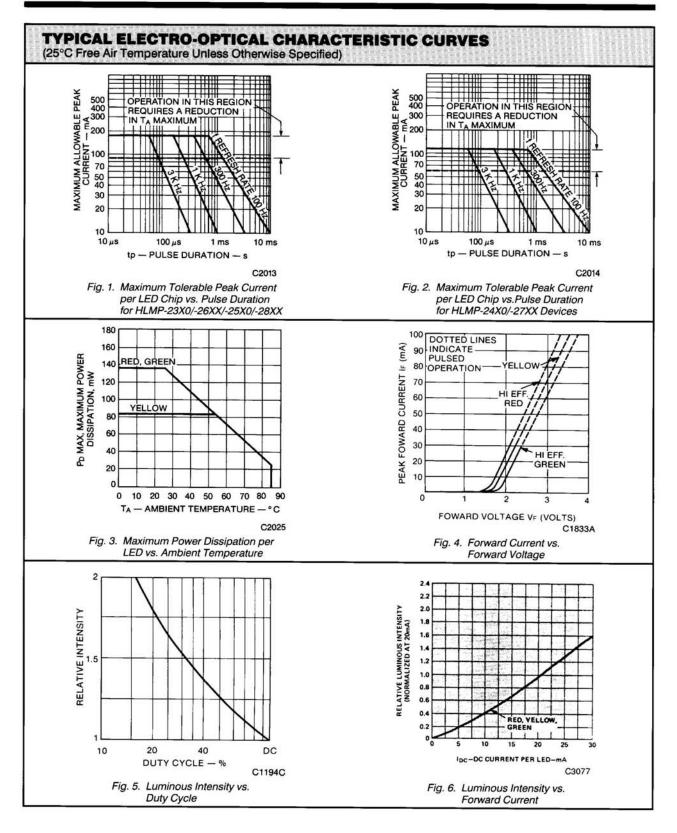
## ELECTRO-OPTICAL CHARACTERISTICS (T\_=25°C)

			HLMP						TEST
PARAMETER		SYMBOL	-2400	-2450	-2755	-2770	-2785	UNIT	CONDITIONS
Luminous Intensity	min.		6	13	13	13	26	mcd	I <sub>F</sub> =20 mA
	typ.	l <sub>v</sub>	20	38	35	35	70	mcd	$I_F = 20 \text{ mA}$
	typ.		33	60	60	60	115	mcd	IF=60 mA pK, 1:3 D.F.
Forward max.	VF	2.6	2.6	2.6	2.6	2.6	v	I⊧=20 mA	
voltage	typ.	VF	2.1	2.1	2.1	2.1	2.1	v	IF=20 MA
Peak wavelength	typ.	$\lambda_{p}$	585	585	585	585	585	nm	
Dominant wavelength	typ.	$\lambda_d$	588	588	588	588	588	nm	
Capacitance	typ.	С	35	35	35	35	35	pF	V <sub>F</sub> =0, f=1 MHz
Reverse voltage	min.	VR	6	6	6	6	6	v	l <sub>e</sub> =100 μA
Thermal resistance	typ.	θ <sub>JL</sub>	150	150	150	150	150	°C/W/ LED chip	

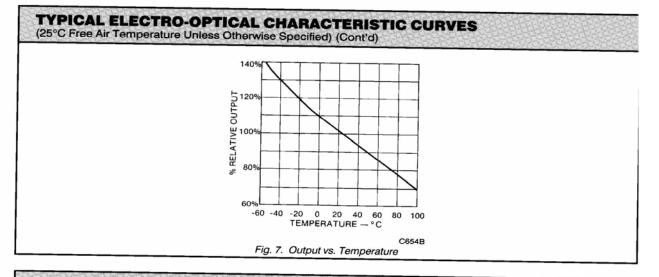
## ELECTRO-OPTICAL CHARACTERISTICS (T\_=25°C)

		SYMBOL	HLMP						TEST
PARAMETER			-2500	-2550	-2855	-2870	-2885	UNIT	CONDITIONS
Luminous	min.	2011 M	5	11	11	11	22	mcd	I⊧=20 mA
Intensity	typ.	typ. I <sub>v</sub>	25	50	50	50	100	mcd	I <sub>F</sub> =20 mA
	typ.		38	75	75	75	150	mcd	IF=60 mA pK, 1:3 D.F
Forward	max.	VF	2.6	2.6	2.6	2.6	2.6	v	I==20 mA
voltage	typ.	VF	2.2	2.2	2.2	2.2	2.2		IF=20 IIIA
Peak wavelength	typ.	$\lambda_{p}$	565	565	565	565	565	nm	
Dominant wavelength	typ.	$\lambda_{d}$	567	567	567	567	567	nm	
Capacitance	typ.	С	40	40	40	40	40	pF	$V_F = 0$ , f=1 MHz
Reverse voltage	min.	V <sub>R</sub>	6	6	6	6	6	v	I <sub>R</sub> =100 μA
Thermal resistance	typ.	θ <sub>JL</sub>	150	150	150	150	150	°C/W/ LED chip	

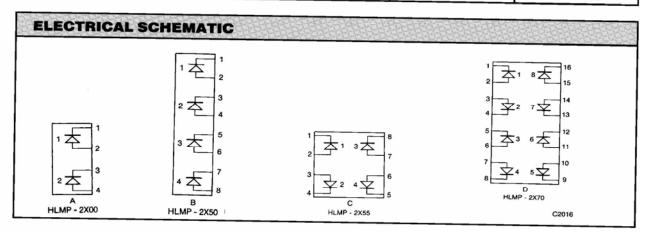








PIN	ELECTRICAL CONNECTION								
	HLMP-2X00	HLMP-2X50	HLMP-2X55	HLMP-2X70/-2X85					
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16	1 Cathode 1 Anode 2 Cathode 2 Anode	1 Cathode 1 Anode 2 Cathode 3 Cathode 3 Anode 4 Cathode 4 Anode	1 Cathode 1 Anode 2 Anode 2 Cathode 3 Cathode 3 Anode 4 Anode 4 Cathode	1 Cathode 1 Anode 2 Anode 2 Cathode 3 Cathode 3 Anode 4 Anode 4 Cathode 5 Cathode 5 Anode 6 Anode 6 Cathode 7 Cathode 7 Cathode 8 Anode 8 Anode 8 Cathode 8 Cathode					





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  - device or system whose failure to perform can be or (b) reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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